



BIPOLAR JUNCTION TRANSISTOR

INTRODUCTION

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TOPIC OUTLINE

Transistor Construction

Transistor Configurations

Regions of Operation



TRANSISTOR CONSTRUCTION



THE FIRST TRANSISTOR



December 23, 1947

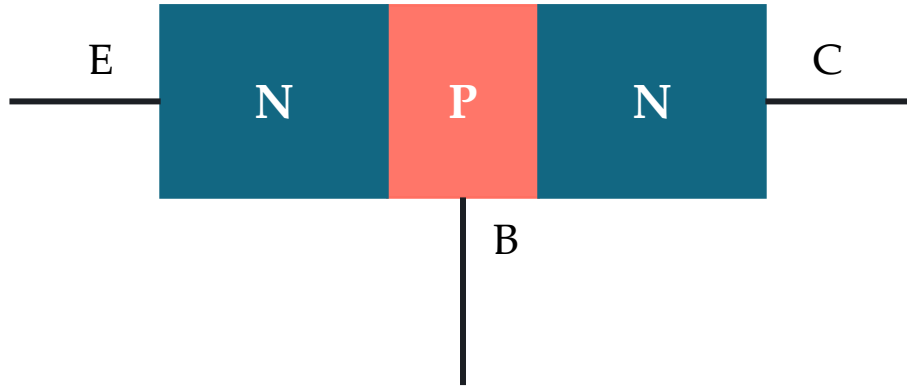
The invention of the transistor, which revolutionized modern electronics was the result of collaborative work by three brilliant scientists:

- **Dr. John Bardeen**
- **Dr. Walter Brattain**
- **Dr. William Shockley**

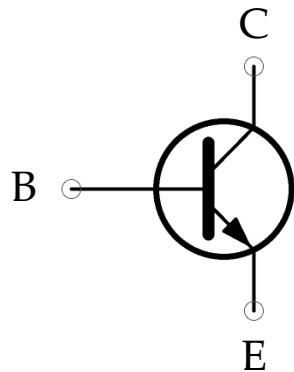


TRANSISTOR CONSTRUCTION

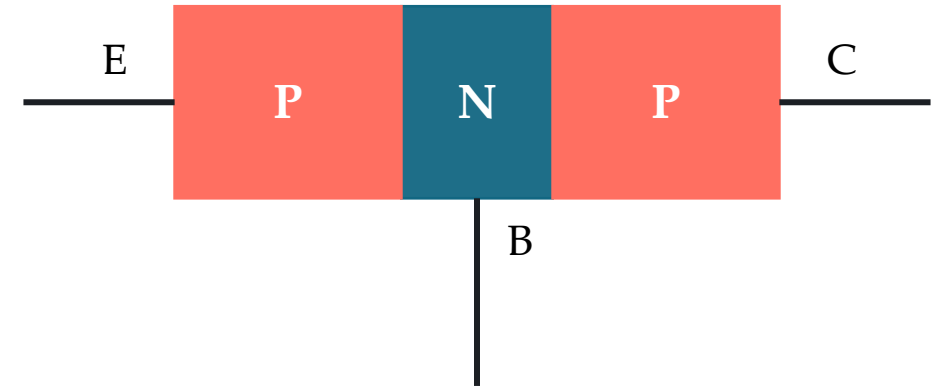
NPN



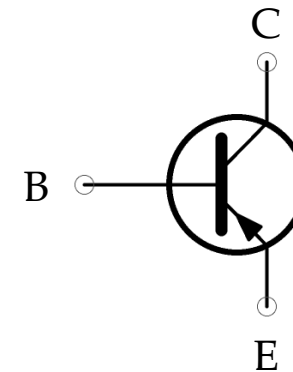
Schematic Symbol



PNP



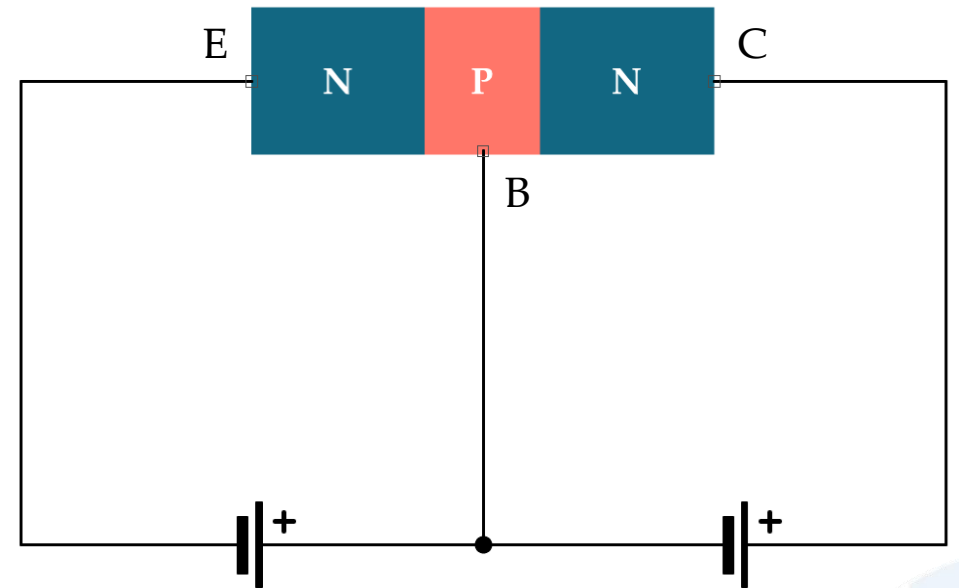
Schematic Symbol



BIPOLAR JUNCTION TRANSISTOR

A Bipolar Junction Transistor (BJT) is a three-terminal semiconductor device that uses both free electrons and holes as charge carriers for its operation.

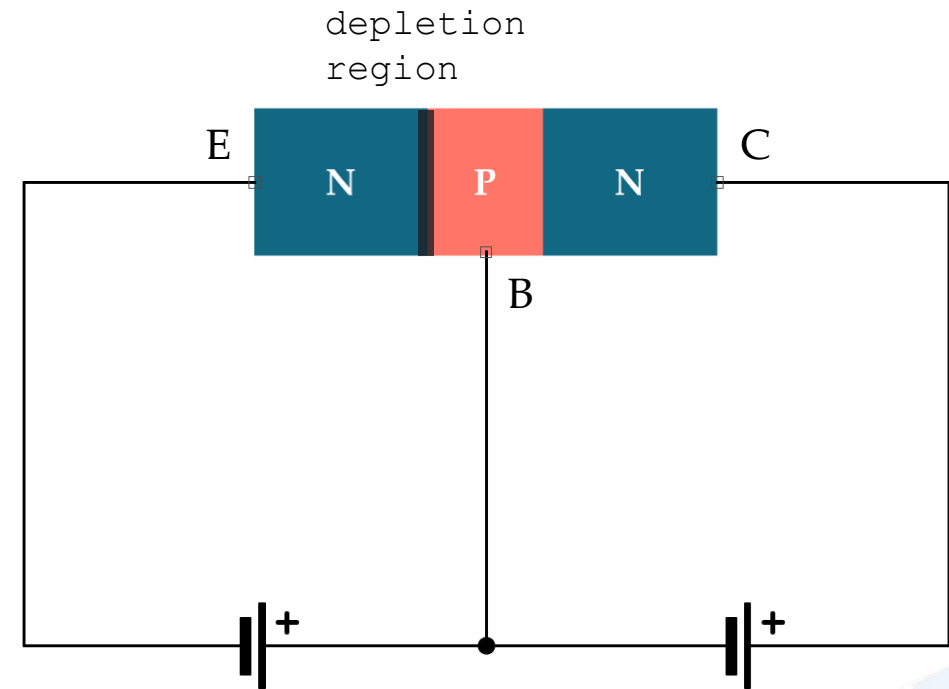
The term “bipolar” means two polarities.



EMITTER-BASE DIODE

The emitter-based diode in a BJT is forward-biased during normal operation.

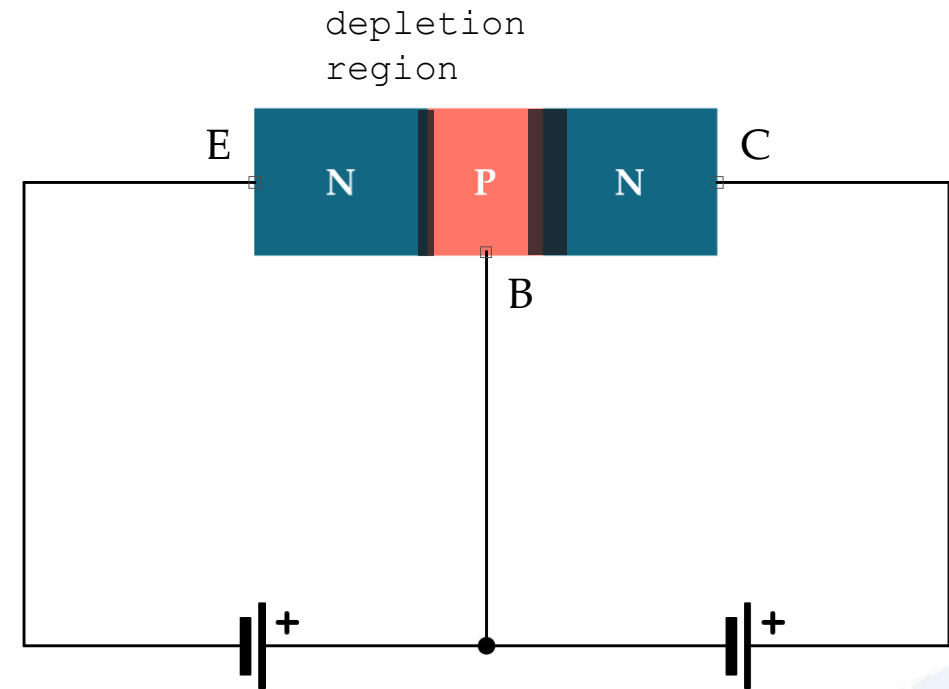
The emitter is heavily doped while base is lightly doped to ensure most carriers reach the collector.



COLLECTOR-BASE DIODE

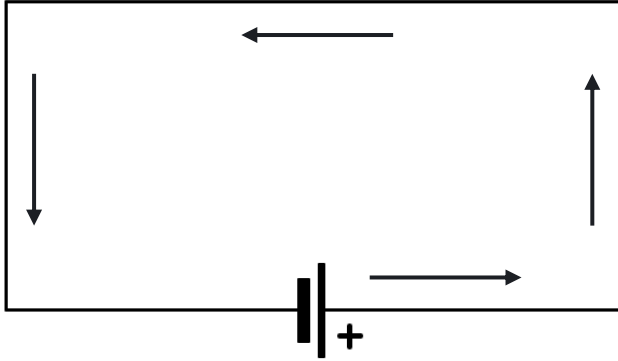
The collector-based diode in a BJT is typically reverse-biased.

The collector is doped at intermediate level – between the lightly doped base and heavily doped emitter.



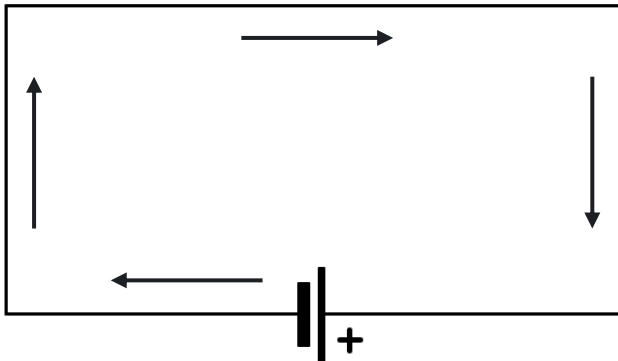
CURRENT FLOW NOTATION

Conventional Flow Notation

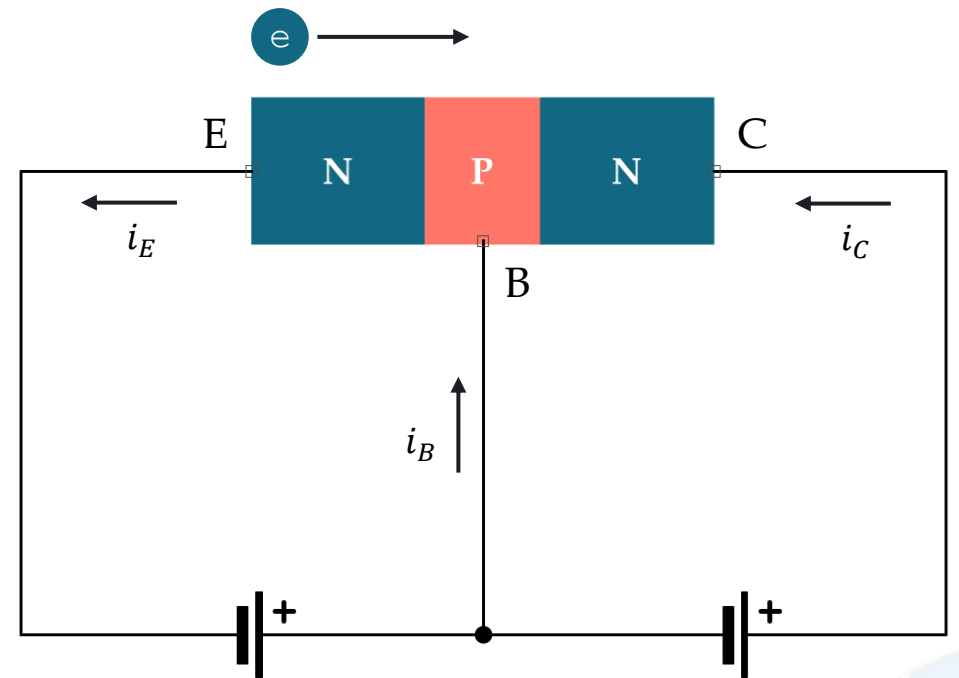


Used in mathematical calculations

Electron Flow Notation



Actual movement of electrons

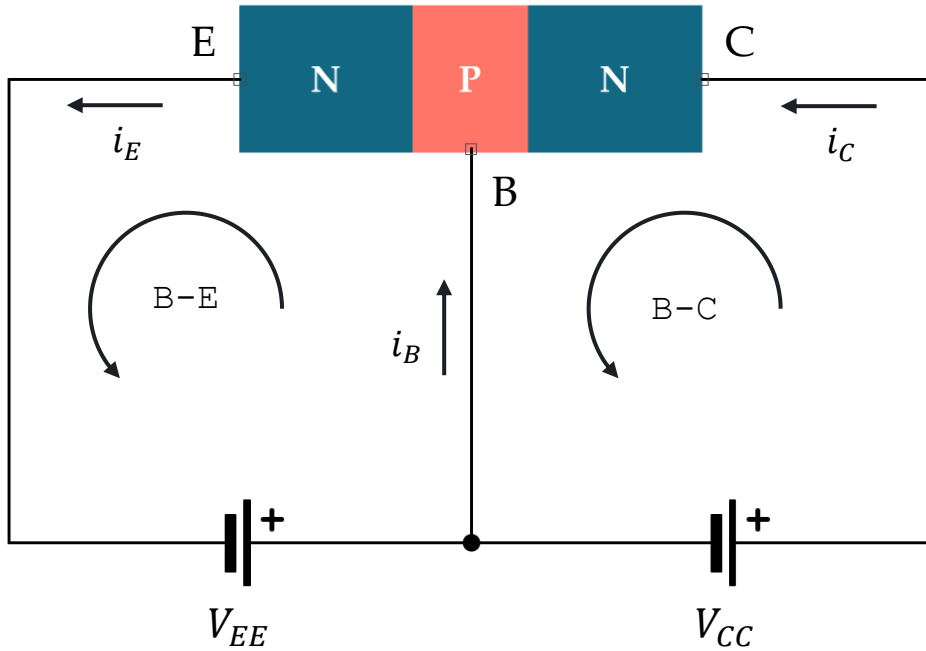


TRANSISTOR CONFIGURATIONS



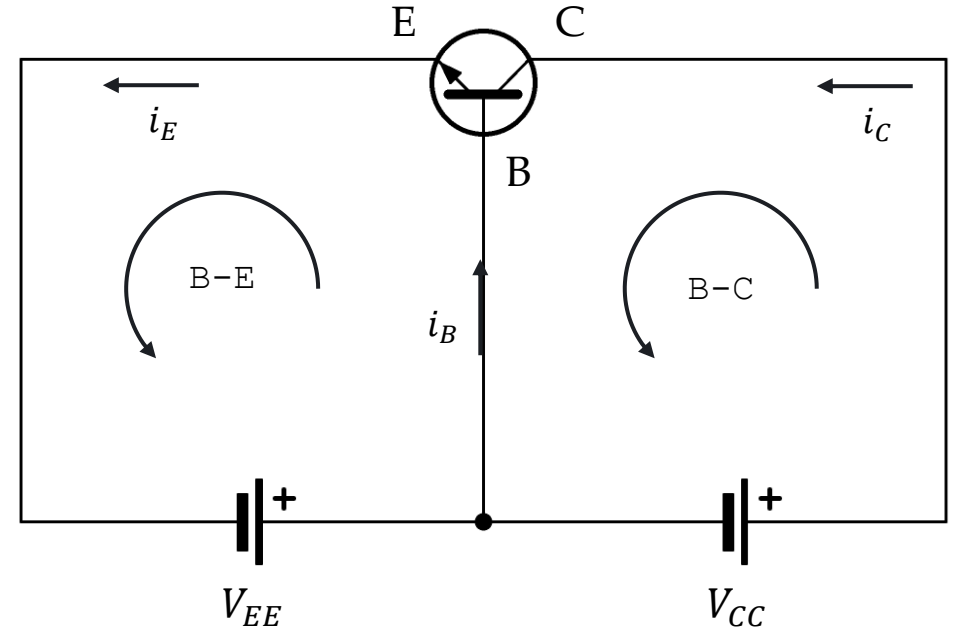
COMMON-BASE

Common-Base Configuration



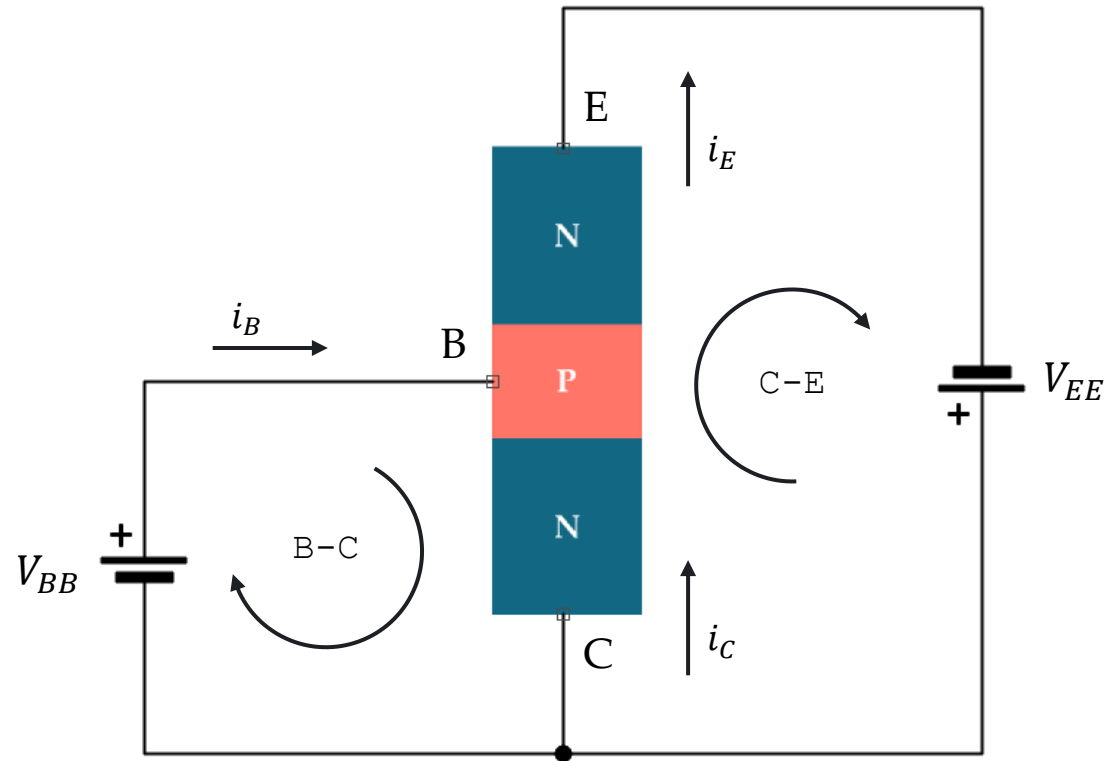
Base is common to both input and output loop.

Circuit Equivalent



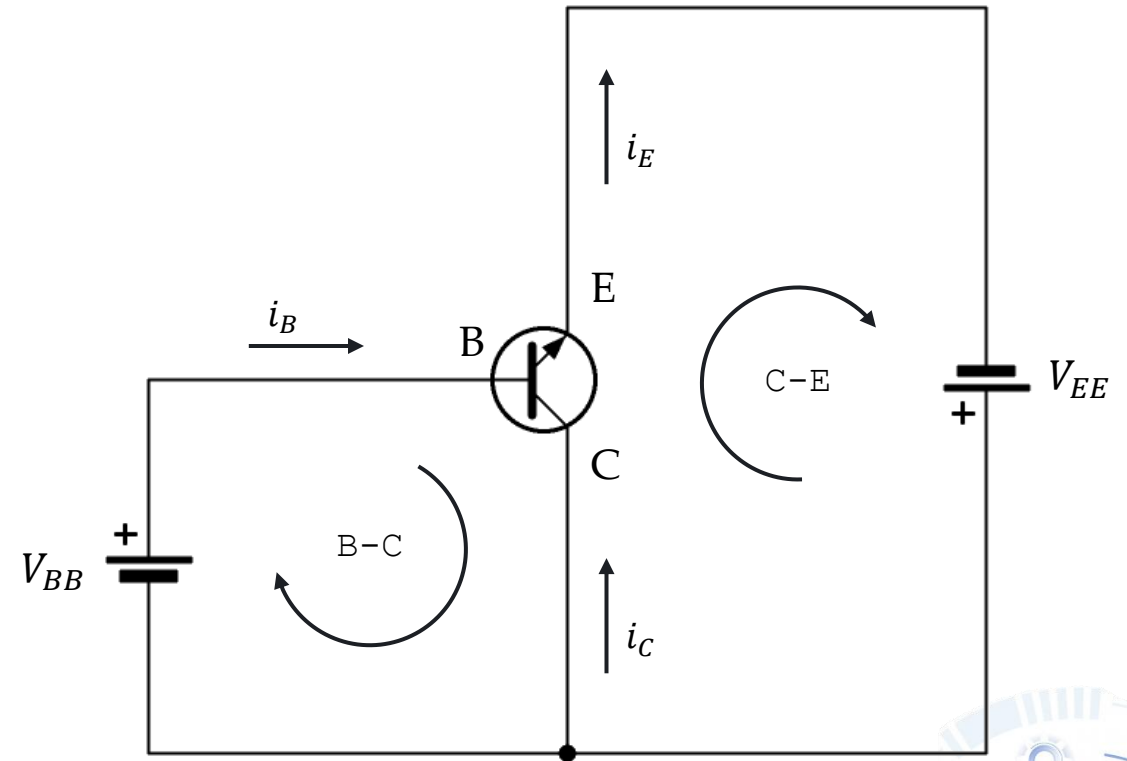
COMMON-COLLECTOR

Common-Collector Configuration



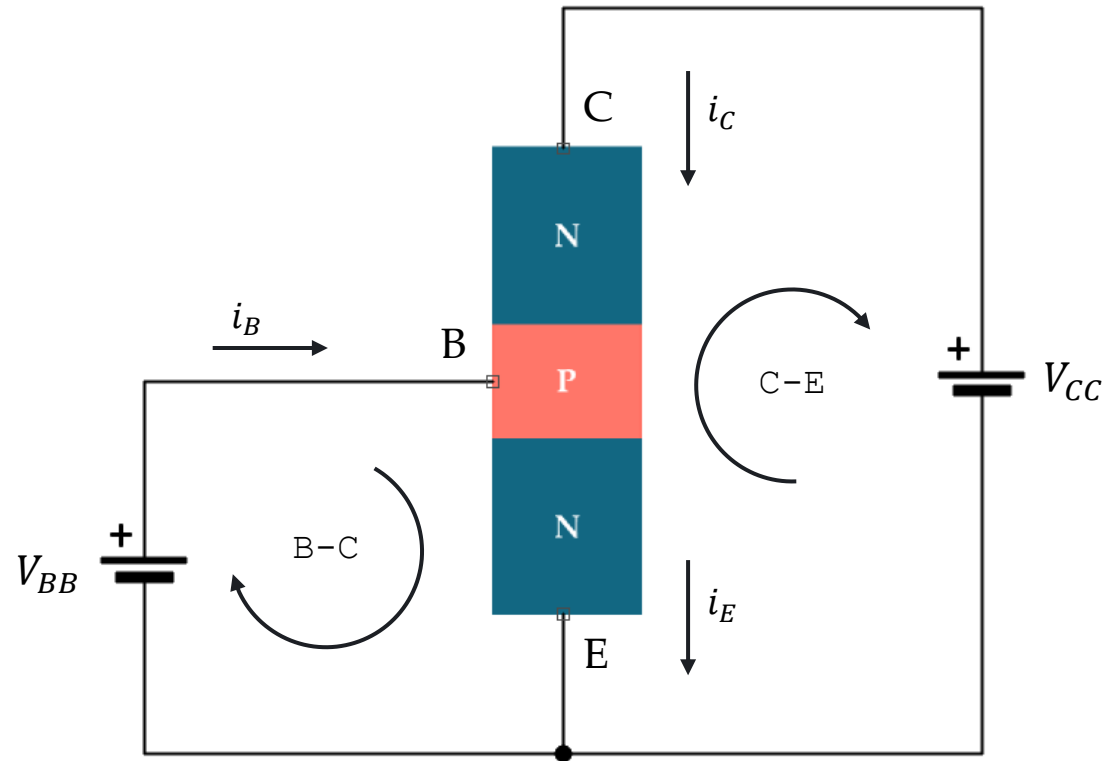
Collector is common to both input and output loop.

Circuit Equivalent



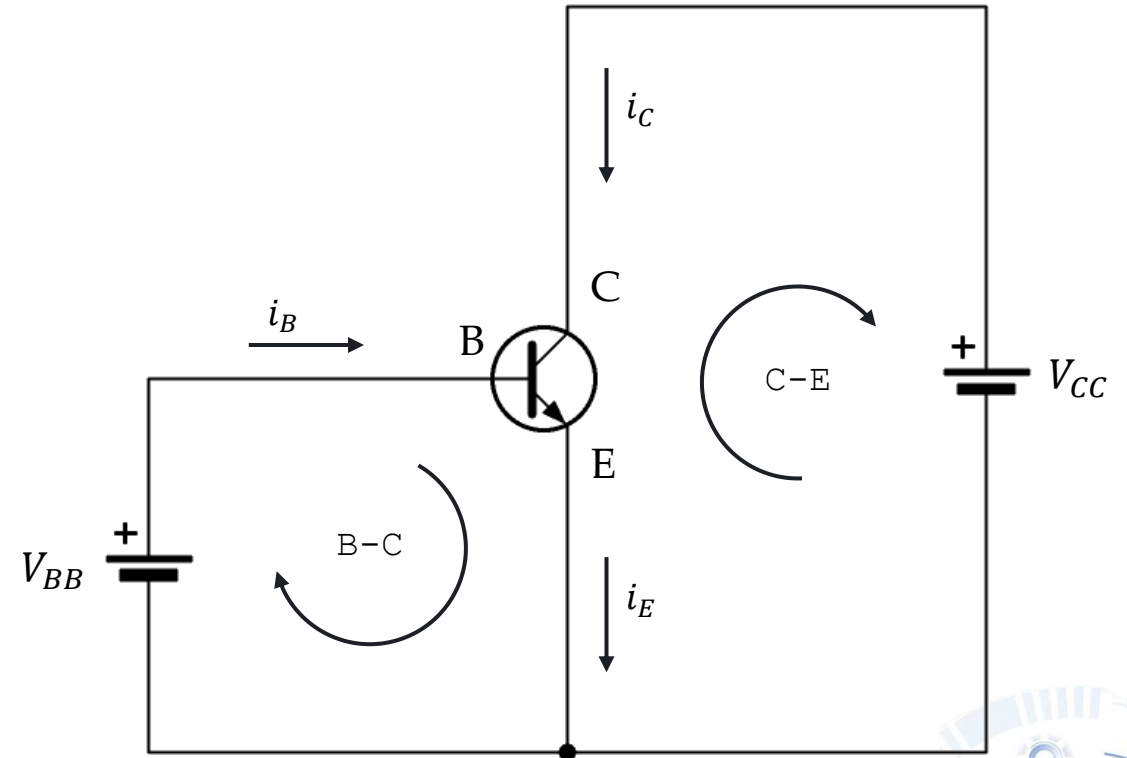
COMMON-EMITTER

Common-Emitter Configuration



Emitter is common to both input and output loop.

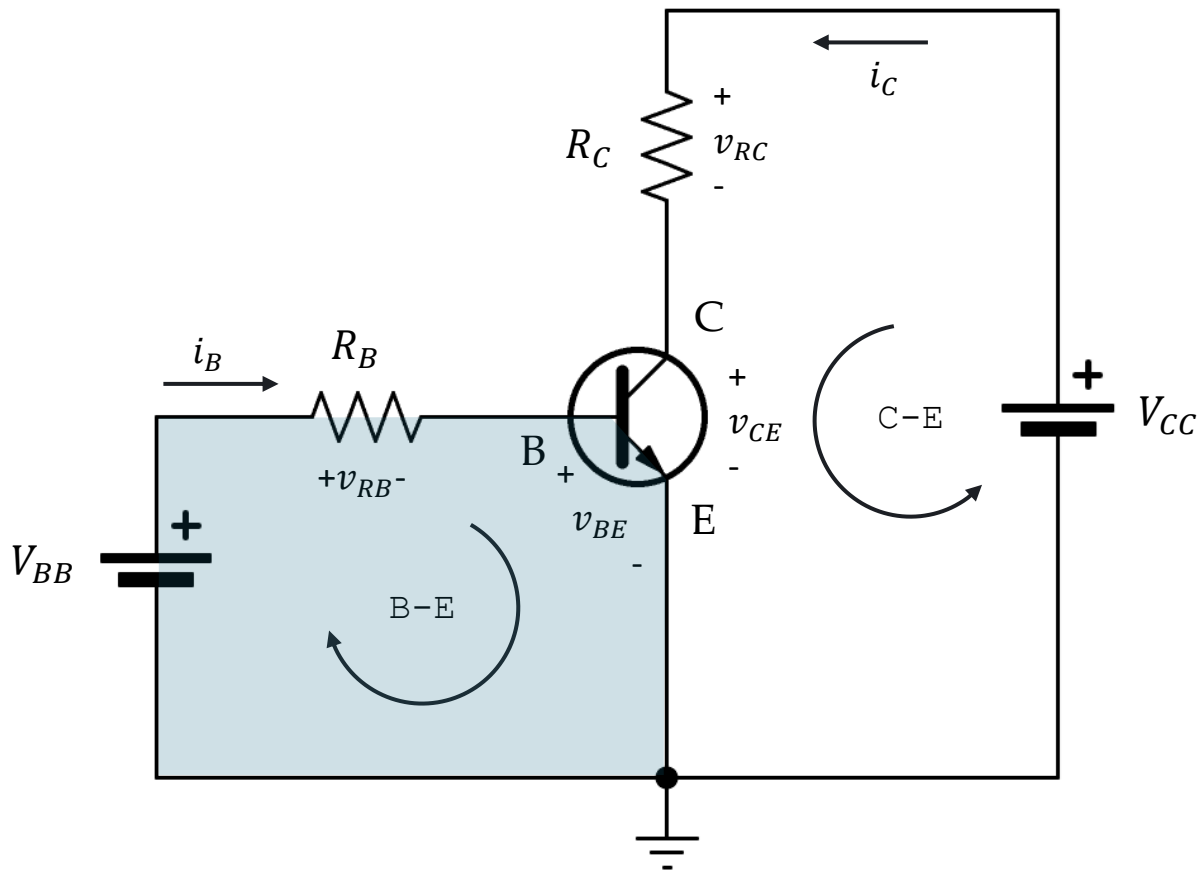
Circuit Equivalent



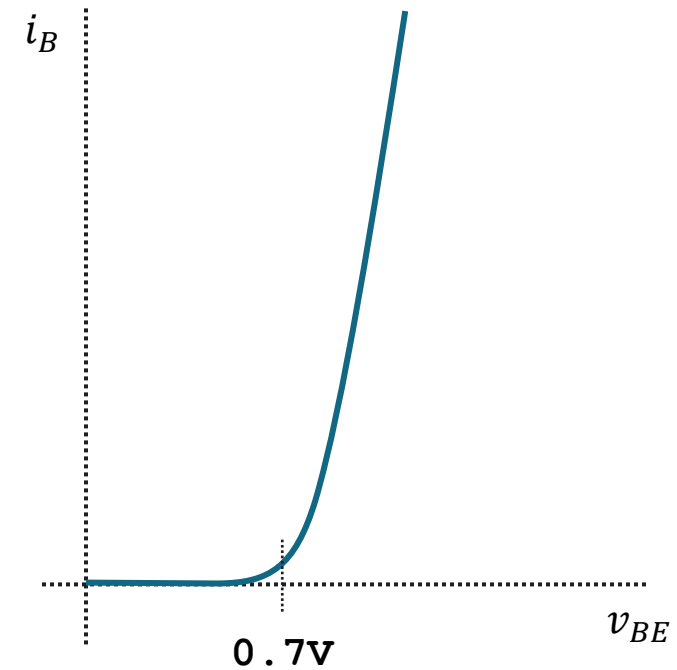
REGIONS OF OPERATION



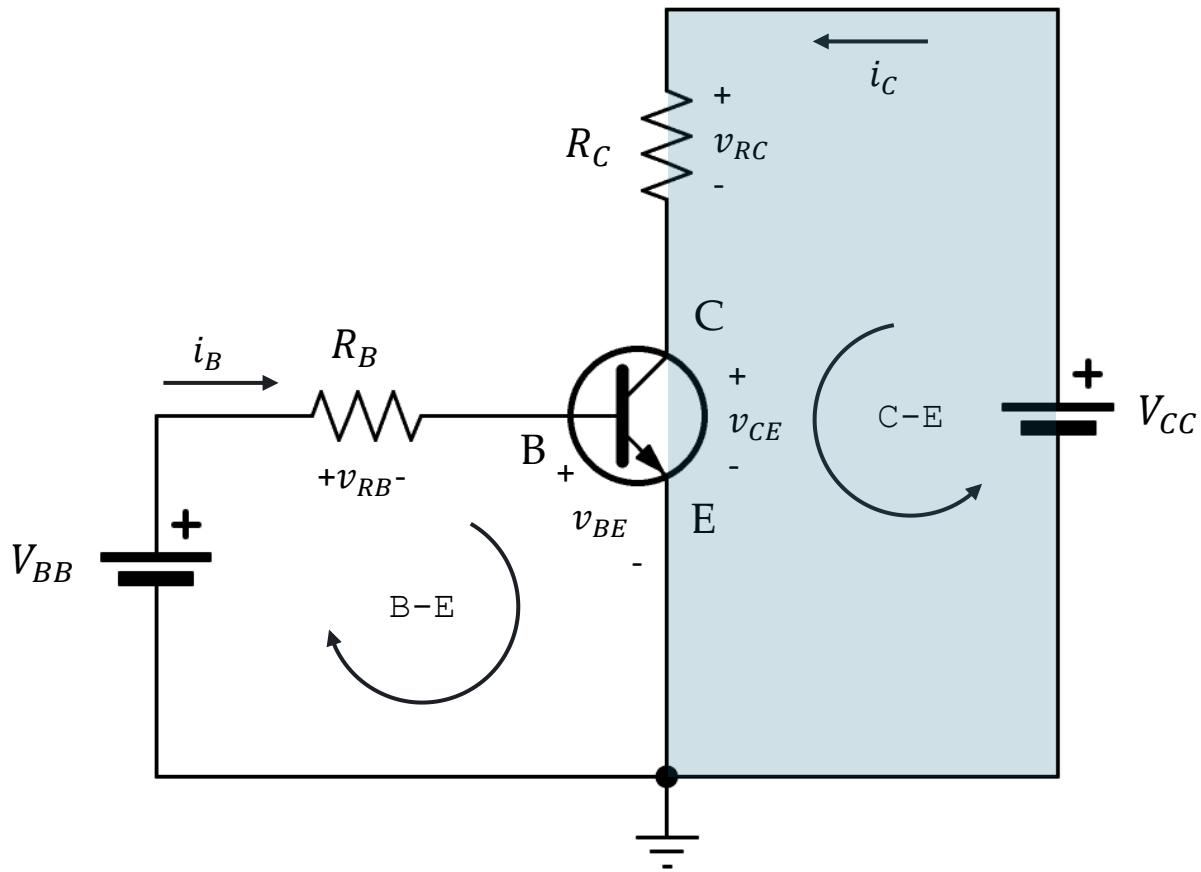
THE BASE CURVE



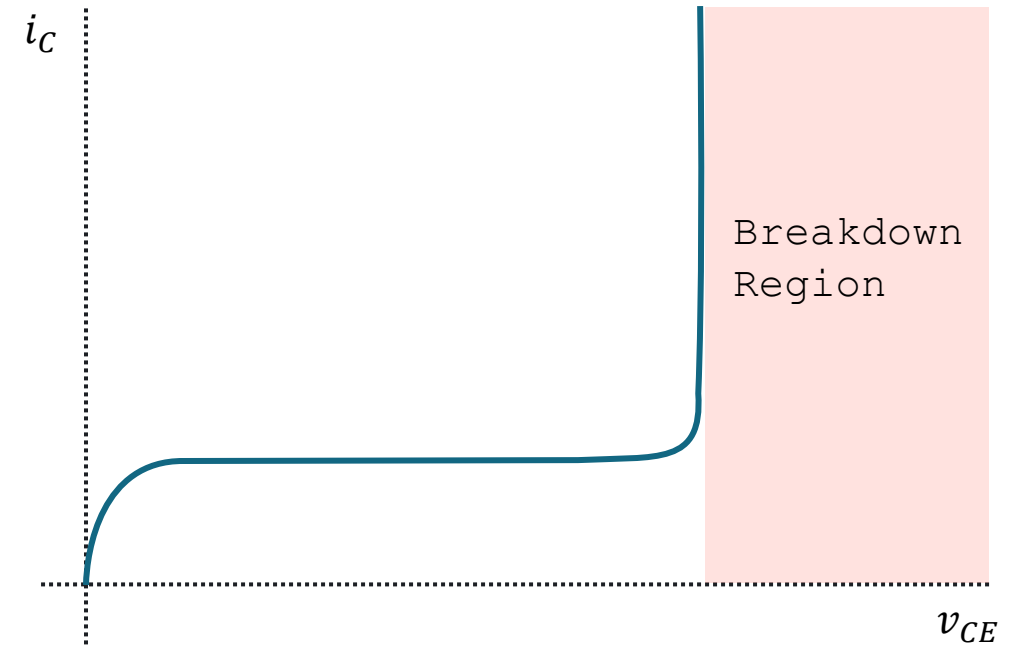
The Base Curve



THE COLLECTOR CURVE

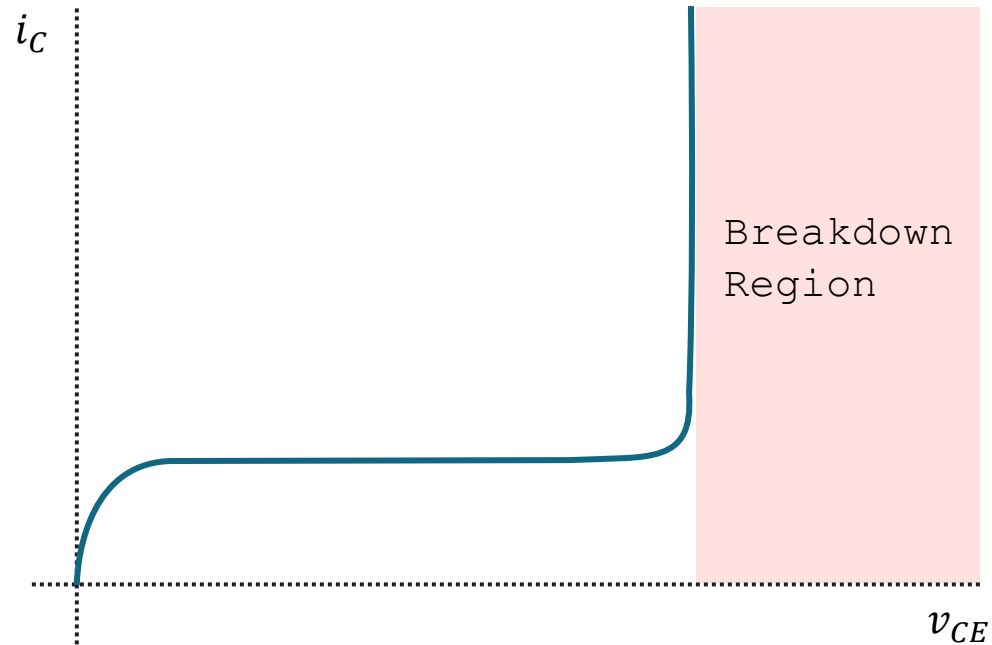


The Collector Curve



BREAKDOWN REGION

Collector Curve



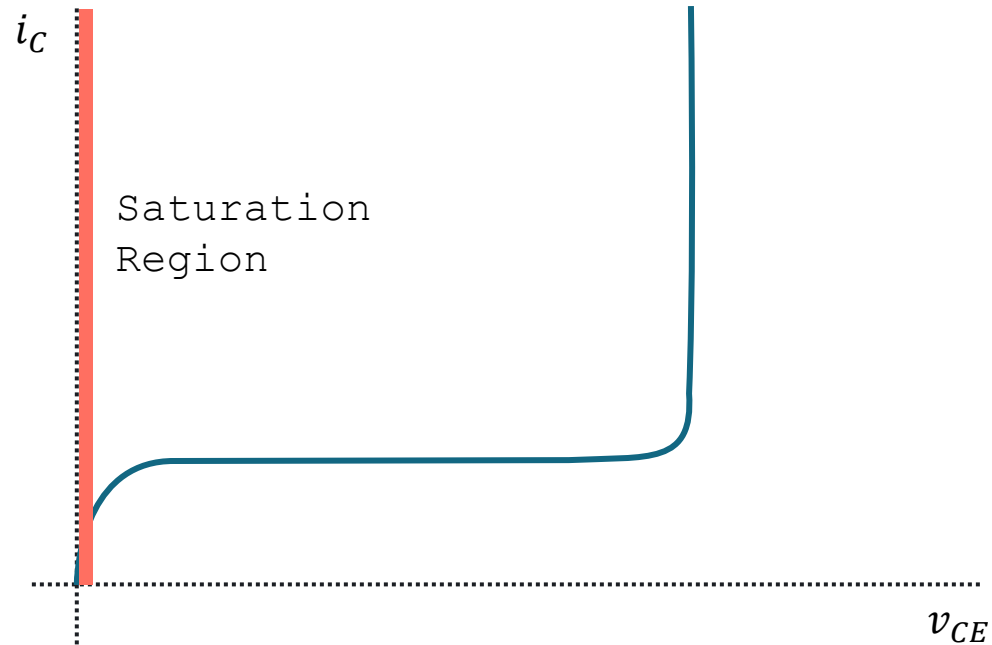
The **breakdown region** is the operating state where the voltage across the transistor's junctions exceeds safe limits, causing a large, uncontrolled current that can **destroy** the device.

A transistor should **never operate** in this region.



SATURATION REGION

Collector Curve



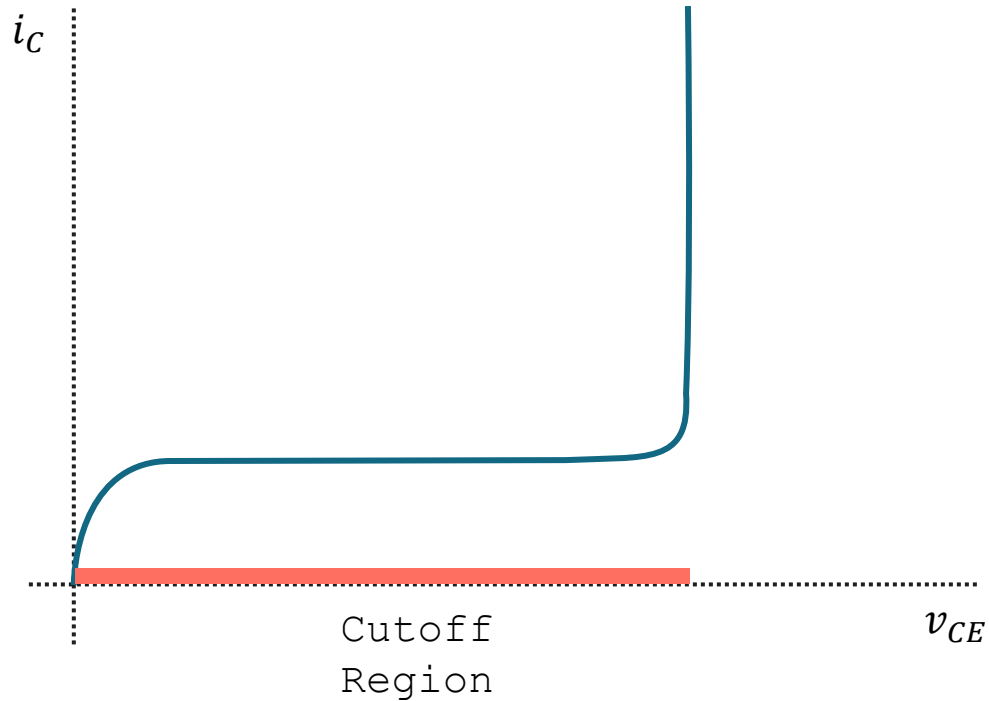
The saturation region is the operating state maximum current flows from collector to emitter, and very low collector-emitter voltage ($v_{CE} \approx 0$).

In this region, the transistor acts like a closed switch.



CUTOFF REGION

Collector Curve



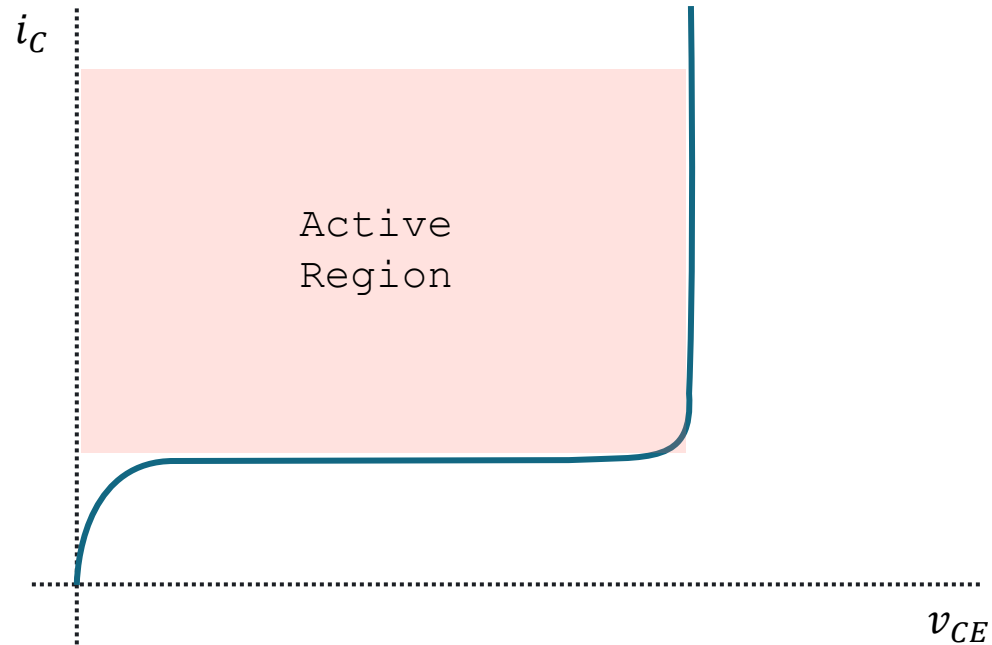
The cutoff region is the operating state of a transistor where the base current is nearly zero ($i_B \approx 0$), resulting in no collector current flow ($i_C \approx 0$).

In this region, the transistor acts like an open switch.



ACTIVE REGION

Collector Curve



The active region is the operating state of a transistor where the collector current is constant.

In this region the transistor functions as an amplifier.



LABORATORY

